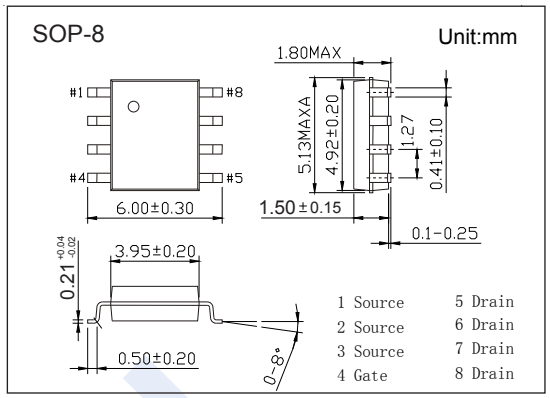
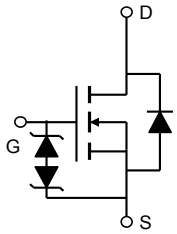
N-Channel MOSFET

AO4498E (KO4498E)



■ Features

- $V_{DS\ (V)}$ = 30V
- I_D = 18 A (V_{GS} = 10V)
- $R_{DS(ON)}$ < 5.8mΩ (V_{GS} = 10V)
- $R_{DS(ON)}$ < 8.5mΩ (V_{GS} = 4.5V)
- ESD Rating: 2KV HBM



■ Absolute Maximum Ratings Ta = 25℃

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current	T_A=25℃	I_D	18	A
	T_A=70℃		14	
Pulsed Drain Current		I_{DM}	120	
Power Dissipation	T_A=25℃	P_D	3.1	W
	T_A=70℃		2	
Thermal Resistance.Junction- to-Ambient	t ≤ 10s	R_{thJA}	40	℃/W
	Steady-State		75	
Thermal Resistance.Junction- to-Lead		R_{thJL}	24	
Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{stg}	-55 to 150	

N-Channel MOSFET

AO4498E (KO4498E)

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	I_D=250μA, V_{GS}=0V	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1	uA
		V_{DS}=30V, V_{GS}=0V, T_J=55℃			5	
Gate-Body Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±10	uA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} , I_D=250uA	1.3		2.3	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=18A			5.8	mΩ
		V_{GS}=10V, I_D=18A T_J=125℃			8.9	
		V_{GS}=5V, I_D=16A			8.5	
On State Drain Current	$I_{D(ON)}$	V_{GS}=10V, V_{DS}=5V	120			A
Forward Transconductance	g_{FS}	V_{DS}=5V, I_D=18A		50		S
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=15V, f=1MHz	1840		2760	pF
Output Capacitance	C_{oss}		230		430	
Reverse Transfer Capacitance	C_{rss}		145		340	
Gate Resistance	R_g	V_{GS}=0V, V_{DS}=0V, f=1MHz	0.6		1.9	Ω
Total Gate Charge (10V)	Q_g	V_{GS}=10V, V_{DS}=15V, I_D=18A	34		50	nC
Total Gate Charge (4.5V)			16		24	
Gate Source Charge	Q_{gs}		5.6		8.4	
Gate Drain Charge	Q_{gd}		6		14	
Turn-On DelayTime	$t_{d(on)}$	V_{GS}=10V, V_{DS}=15V, R_L=0.83Ω, R_{GEN}=3Ω		8		ns
Turn-On Rise Time	t_r			10		
Turn-Off DelayTime	$t_{d(off)}$			33		
Turn-Off Fall Time	t_f			8		
Body Diode Reverse Recovery Time	t_{rr}	I_F= 18A, dI/dt= 500A/us	10		15	
Body Diode Reverse Recovery Charge	Q_{rr}		22		32	nC
Maximum Body-Diode Continuous Current	I_S				4	A
Diode Forward Voltage	V_{SD}	I_S=1A,V_{GS}=0V			1	V

Note : The static characteristics in Figures 1 to 6 are obtained using <300 us pulses, duty cycle 0.5% max.

■ Marking

Marking	4498E KC****

N-Channel MOSFET

AO4498E (KO4498E)

■ Typical Characterisitics

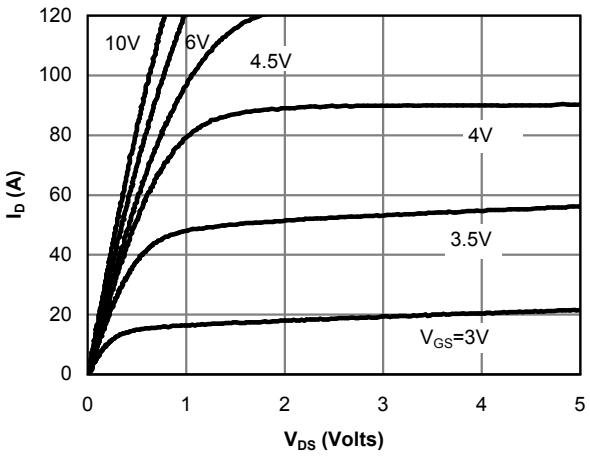


Fig 1: On-Region Characteristics (Note E)

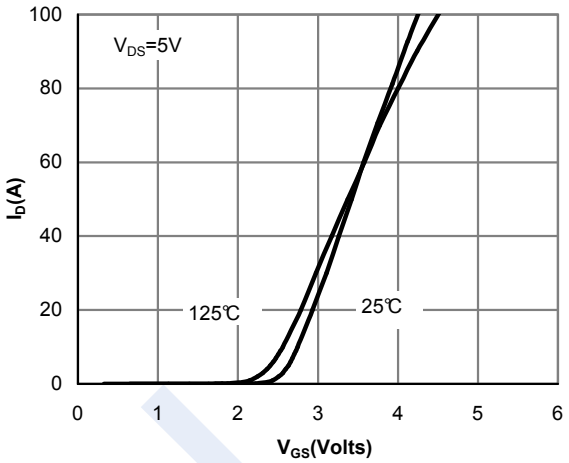


Figure 2: Transfer Characteristics (Note E)

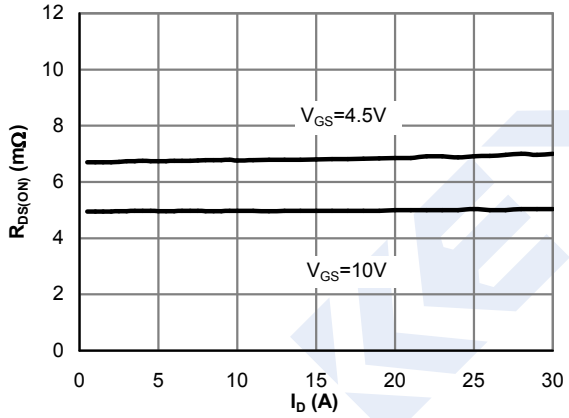


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

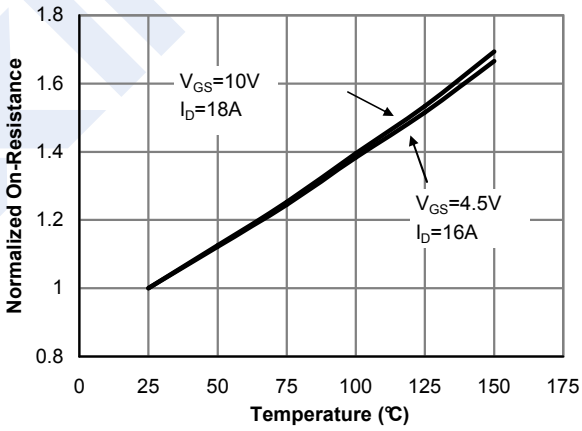


Figure 4: On-Resistance vs. Junction Temperature (Note E)

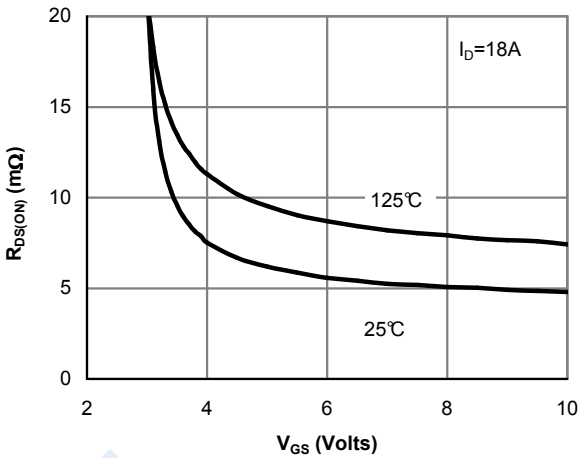


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

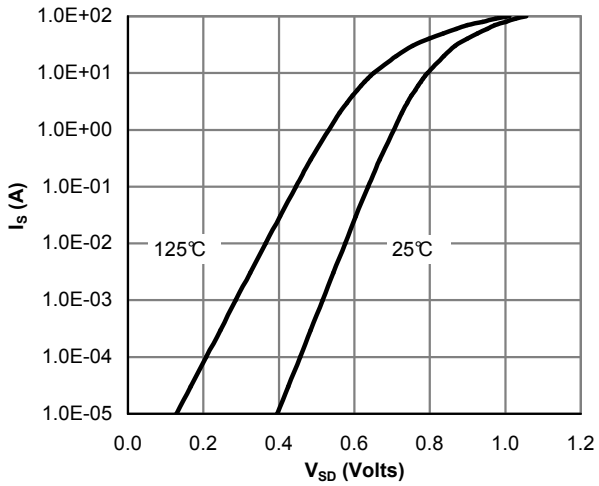


Figure 6: Body-Diode Characteristics (Note E)

N-Channel MOSFET

AO4498E (KO4498E)

■ Typical Characterisitics

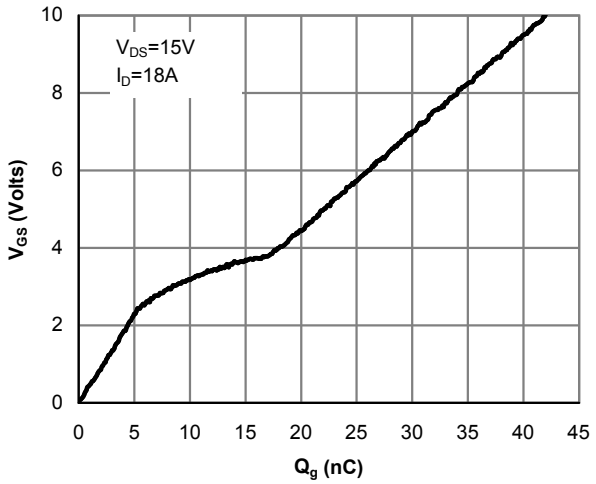


Figure 7: Gate-Charge Characteristics

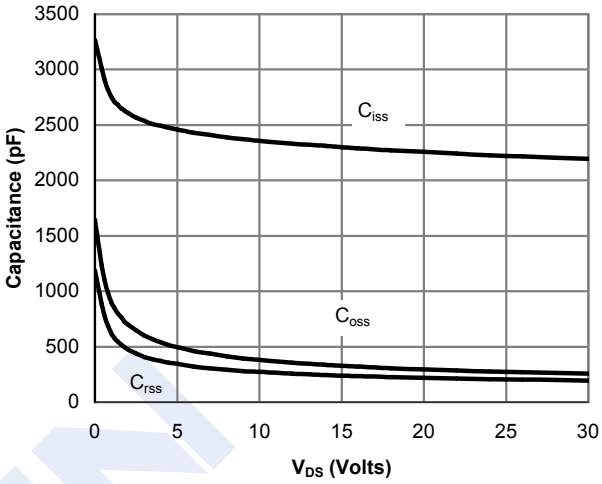


Figure 8: Capacitance Characteristics

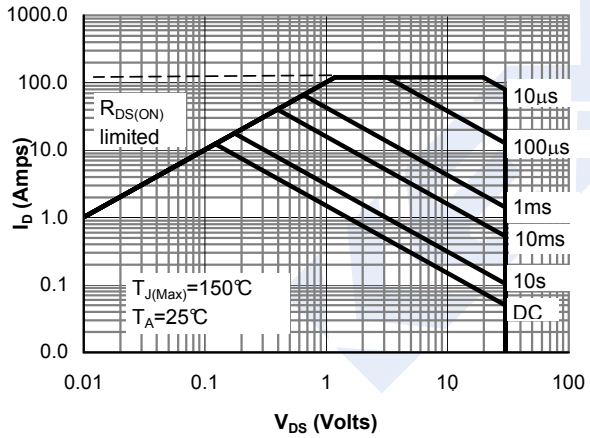


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

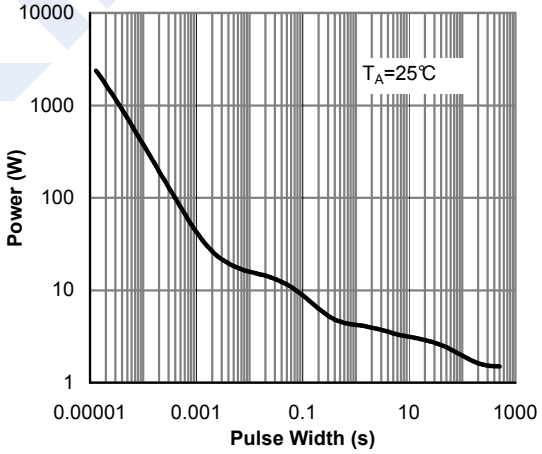


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

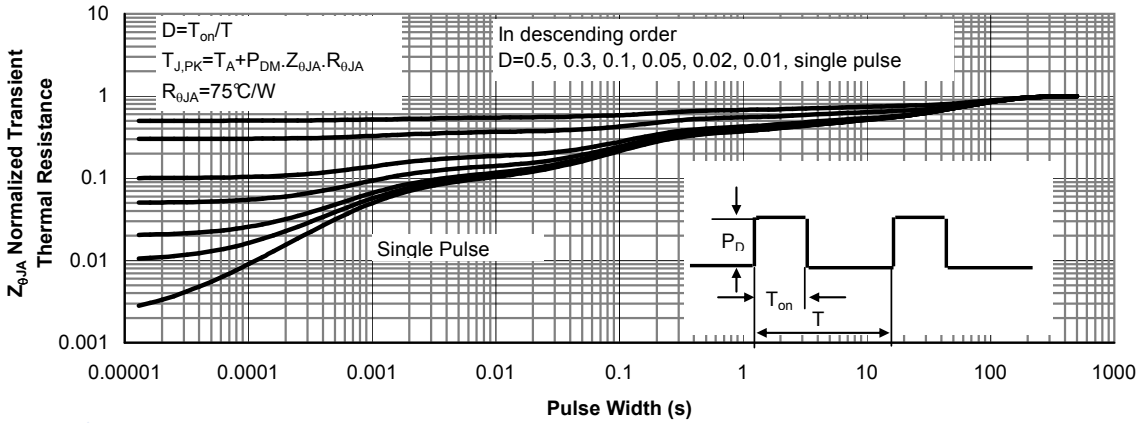


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)